



TQS0522P

The TQS0522P TVS array is designed to protect sensitive electronics from damage or latch-up due to ESD and other voltage-induced transient events. It is designed for use in applications where board space is at a premium. Each device will protect up to two lines. It is unidirectional devices and may be used on lines where the signal polarities are above ground. TVS Diode Array For ESD and Latch-Up Protection

It has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events),and EFT (electrical fast transients).

Features

- Peak Power Dissipation – 30 W (8 x 20 us Waveform)
- Stand-off Voltage: 5.0 V
- Low capacitance (<0.5pF) for high-speed interfaces
- No insertion loss to 3.0GHz
- Protects I/O Port
- Low Clamping Voltage
- Low Leakage
- Low Capacitance
- Meets MSL 1 Requirements
- ROHS compliant
- TECHIP technology

Main applications

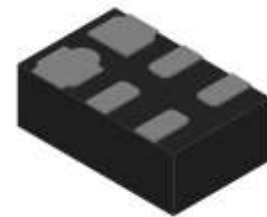
- High Speed Line :USB1.0/2.0/3.0/3.1, VGA, DVI, SDI,
- High Definition Multi-Media Interface (HDMI1.3/1.4/2.0)
- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals

Protection solution to meet

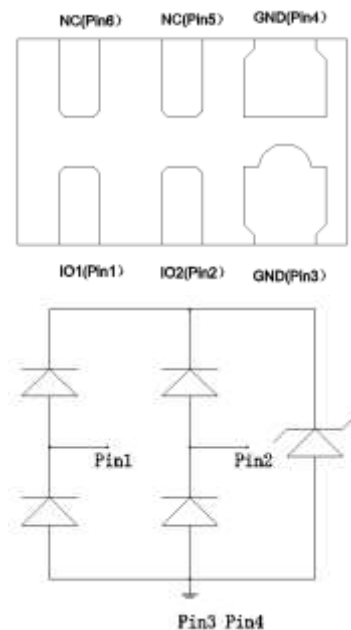
- IEC61000-4-2 (ESD) $\pm 30\text{kV}$ (air), $\pm 20\text{kV}$ (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (Lightning) 3A (8/20 μs)

Ordering Information

Device	Marking	Qty per Reel	Reel Size
TQS0522P	2R2P	3000	7 Inch



DFN1610-6L



Pin Configuration (Top View)

Maximum ratings (Tamb=25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P _{PPP}	30	Watts
ESD Rating per IEC61000-4-2:		20	KV
Contact Air		30	
Lead Soldering Temperature	T _L	260 (10 sec.)	°C
Operating Temperature Range	T _J	-55 ~ 150	°C
Storage Temperature Range	T _{STG}	-55 ~ 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

**Other voltages may be available upon request.*

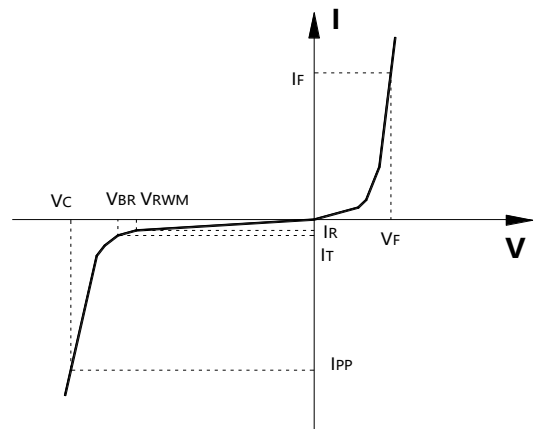
1. *Non-repetitive current pulse, per Figure 1.*

Electrical characteristics (Tamb=25°C Unless Otherwise Specified)

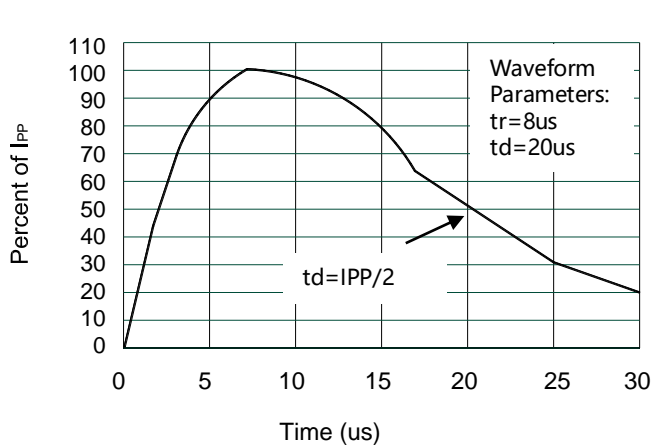
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V _{RWM}	Reverse Working Voltage	Any I/O to Ground			5.0	V
V _{BR}	Reverse Breakdown Voltage	IT = 1mA, Any I/O to Ground	6.0			V
I _R	Reverse Leakage Current	V _{RWM} = 5V, Any I/O to Ground			1	μA
V _F	Diode Forward Voltage	IF = 15mA		0.85	1.2	V
V _C	Clamping Voltage	I _{PP} = 1A, tp =8/20μs, any I/O pin to Ground		8.7		V
		I _{PP} =3A, tp =8/20μs, any I/O pin to Ground		10.7	12	V
I _{PP}	Peak Pulse Current	tp =8/20μs			3	A
C _J	Junction Capacitance	V _R = 0V, f = 1MHz, any I/O pin to Ground		0.3	0.5	pF

Junction capacitance is measured in $V_R=0V, F=1MHz$.

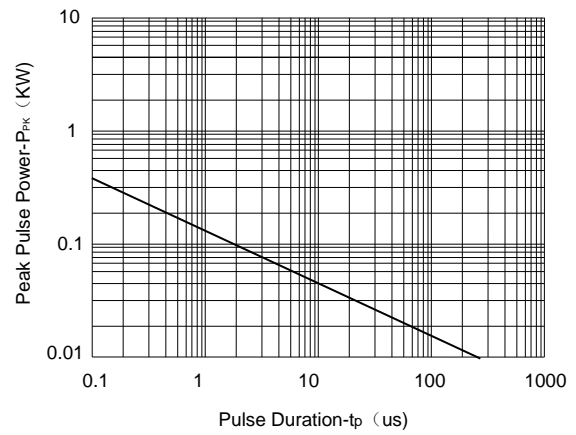
Symbol	Parameter
V_{RWM}	Working Peak Reverse Voltage
V_{BR}	Breakdown Voltage @ I_T
V_C	Clamping Voltage @ I_{PP}
I_T	Test Current
I_{RM}	Leakage current at V_{RWM}
I_{PP}	Peak pulse current
C_O	Off-state Capacitance
C_J	Junction Capacitance



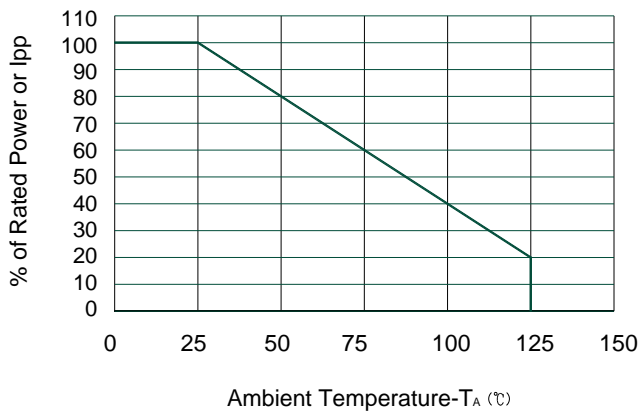
Typical electrical characterist applications



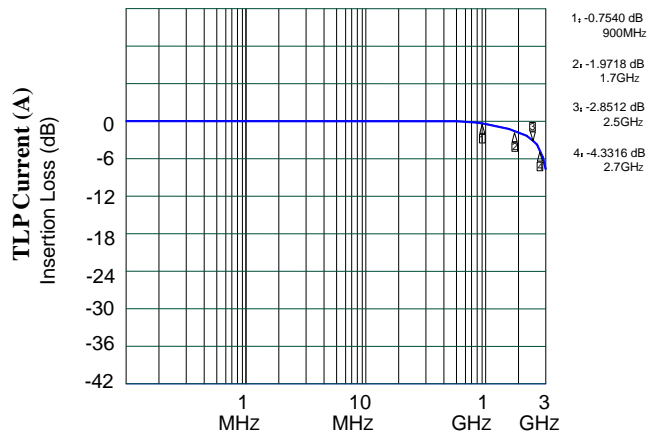
Pulse Waveform



Non-Repetitive Peak Pulse Power vs. Pulse Time



Power Derating Curve



Insertion Loss S21

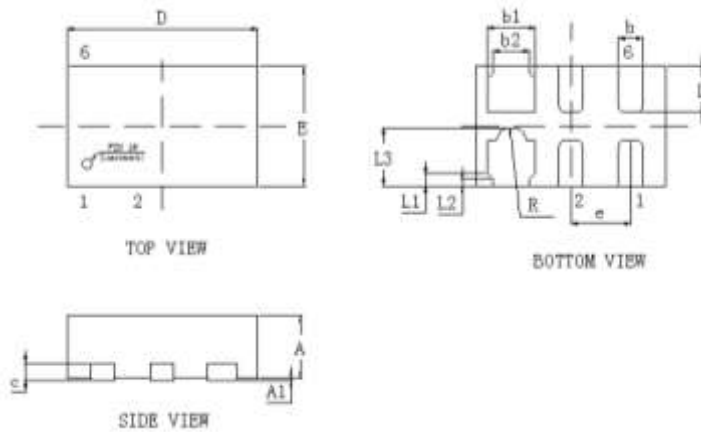
Package Information

DFN1610-6L

Mechanical Data

Case:DFN1610-6L

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters		
	Min	NOM	Max
A	0.50	0.55	0.60
A1	-	0.02	0.05
b	0.15	0.20	0.25
b1	0.35	0.40	0.45
b2	0.20	0.25	0.30
c	0.10	0.15	0.20
D	1.55	1.60	1.65
e	0.50BSC		
E	0.95	1.00	1.05
L	0.33	0.38	0.43
L1	0.100REF		
L2	0.05REF		
L3	0.49REF		
R	0.08	0.13	0.18

Recommended Pad outline

